

# RGTH80TK65

### 650V 40A Field Stop Trench IGBT

V <sub>CES</sub>	650V
I <sub>C(100°C)</sub>	19A
V <sub>CE(sat) (Typ.)</sub>	1.6V@I <sub>C</sub> =40A
$P_D$	66W

#### Features

- 1) Low Collector Emitter Saturation Voltage
- 2) High Speed Switching
- 3) Low Switching Loss & Soft Switching
- 4) Pb free Lead Plating; RoHS Compliant

### Applications

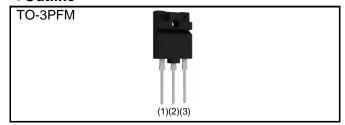
**PFC** 

**UPS** 

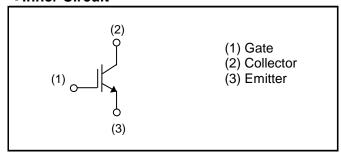
**Power Conditioner** 

ΙH

#### Outline



### ●Inner Circuit



Packaging Specifications

	Packaging	Tube
	Reel Size (mm)	-
Tuno	Tape Width (mm)	-
Type	Basic Ordering Unit (pcs)	450
	Packing Code	C11
	Marking	RGTH80TK65

### ● Absolute Maximum Ratings (at T<sub>C</sub> = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Collector - Emitter Voltage		V <sub>CES</sub>	650	V
Gate - Emitter Voltage		$V_{GES}$	±30	V
Collector Current	T <sub>C</sub> = 25°C	I <sub>C</sub>	31	А
	T <sub>C</sub> = 100°C	I <sub>C</sub>	19	А
Pulsed Collector Current		I <sub>CP</sub> *1	160	А
Power Dissipation	T <sub>C</sub> = 25°C	P <sub>D</sub>	66	W
	T <sub>C</sub> = 100°C	P <sub>D</sub>	33	W
Operating Junction Temperature		T <sub>j</sub>	-40 to +175	°C
Storage Temperature		T <sub>stg</sub>	-55 to +175	°C

<sup>\*1</sup> Pulse width limited by T<sub>jmax.</sub>

### ●Thermal Resistance

Doromotor	Symbol	Values			Unit
Parameter		Min.	Тур.	Max.	Offic
Thermal Resistance IGBT Junction - Case	$R_{\theta(j-c)}$	-	-	2.27	°C/W

## ullet IGBT Electrical Characteristics (at $T_j = 25$ °C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Тур.	Max.	Uniit
Collector - Emitter Breakdown Voltage	BV <sub>CES</sub>	$I_{C} = 10 \mu A, V_{GE} = 0 V$	650	1	-	V
Collector Cut - off Current	I <sub>CES</sub>	$V_{CE} = 650V, V_{GE} = 0V$	ı	1	10	μΑ
Gate - Emitter Leakage Current	I <sub>GES</sub>	$V_{GE} = \pm 30V, \ V_{CE} = 0V$	ı	ı	±200	nA
Gate - Emitter Threshold Voltage	$V_{\text{GE(th)}}$	$V_{CE} = 5V, I_{C} = 27.6 \text{mA}$	4.5	5.5	6.5	V
Collector - Emitter Saturation Voltage	V <sub>CE(sat)</sub>	$I_C = 40A$ , $V_{GE} = 15V$ $T_j = 25$ °C $T_j = 175$ °C	-	1.6 2.1	2.1	V

# ●IGBT Electrical Characteristics (at T<sub>j</sub> = 25°C unless otherwise specified)

Daramatar	Cymah al	Conditions	Values			l limit
Parameter	Symbol		Min.	Тур.	Max.	Unit
Input Capacitance	C <sub>ies</sub>	V <sub>CE</sub> = 30V	-	2210	-	
Output Capacitance	C <sub>oes</sub>	$V_{GE} = 0V$	-	85	-	pF
Reverse Transfer Capacitance	$C_{res}$	f = 1MHz	-	35	-	
Total Gate Charge	Q <sub>g</sub>	V <sub>CE</sub> = 300V	-	79	-	
Gate - Emitter Charge	$Q_{ge}$	I <sub>C</sub> = 40A	-	21	-	nC
Gate - Collector Charge	$Q_{gc}$	V <sub>GE</sub> = 15V	-	29	-	
Turn - on Delay Time	t <sub>d(on)</sub>	$I_C = 40A, V_{CC} = 400V$	-	34	-	
Rise Time	t <sub>r</sub>	$V_{GE} = 15V, R_G = 10\Omega$	-	50	-	
Turn - off Delay Time	t <sub>d(off)</sub>	T <sub>j</sub> = 25°C	-	120	-	ns
Fall Time	t <sub>f</sub>	Inductive Load	-	47	-	
Turn - on Delay Time	t <sub>d(on)</sub>	$I_C = 40A, V_{CC} = 400V$	-	34	-	
Rise Time	t <sub>r</sub>	$V_{GE} = 15V, R_G = 10\Omega$	-	50	-	
Turn - off Delay Time	t <sub>d(off)</sub>	T <sub>j</sub> = 175°C	-	135	-	ns
Fall Time	t <sub>f</sub>	Inductive Load	-	59	-	
		I <sub>C</sub> = 160A, V <sub>CC</sub> = 520V				
Reverse Bias Safe Operating Area	RBSOA	$V_P = 650 \text{V}, V_{GE} = 15 \text{V}$	FULL SQUARE			-
		$R_G = 60\Omega, T_j = 175^{\circ}C$				

Fig.1 Power Dissipation vs. Case Temperature

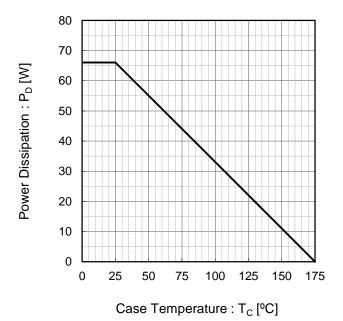


Fig.2 Collector Current vs. Case Temperature

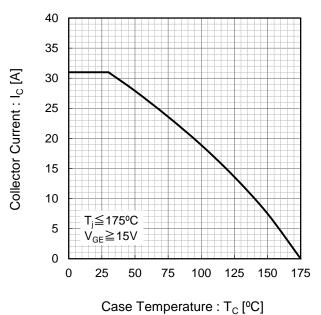


Fig.3 Forward Bias Safe Operating Area

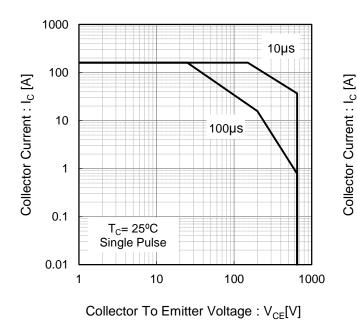
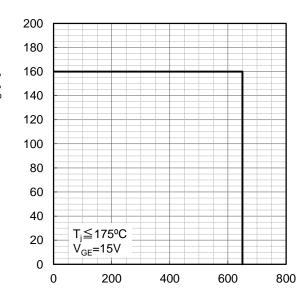


Fig.4 Reverse Bias Safe Operating Area



Collector To Emitter Voltage :  $V_{CE}[V]$ 

Fig.5 Typical Output Characteristics

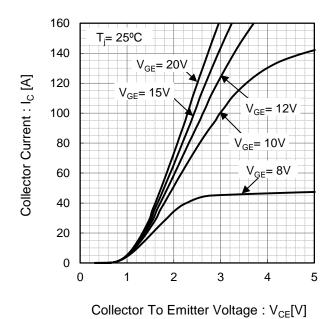
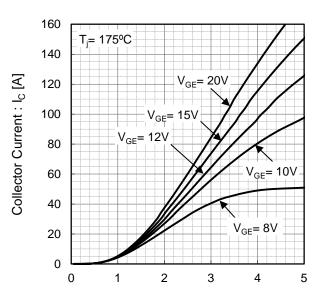


Fig.6 Typical Output Characteristics



Collector To Emitter Voltage : V<sub>CE</sub>[V]

Fig.7 Typical Transfer Characteristics

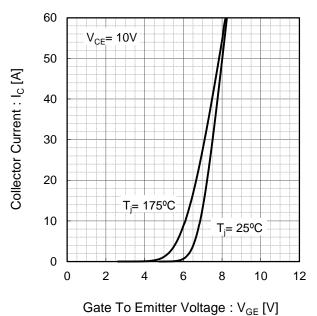


Fig.8 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature

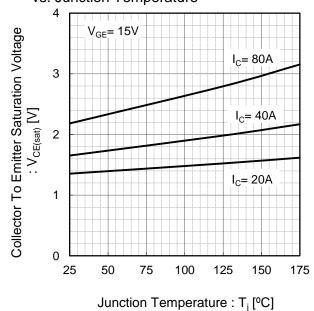
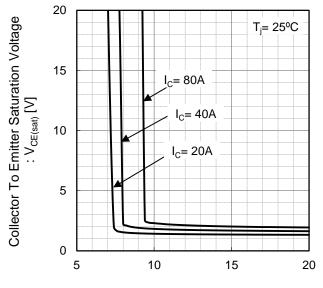
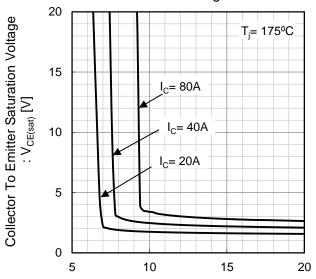


Fig.9 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage

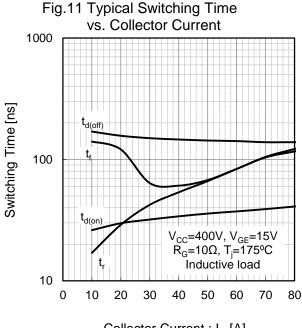


Gate To Emitter Voltage : V<sub>GE</sub> [V]

Fig.10 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage



Gate To Emitter Voltage : V<sub>GE</sub> [V]



Collector Current : I<sub>C</sub> [A]

Fig.12 Typical Switching Time vs. Gate Resistance 1000 Switching Time [ns] 100  $V_{CC}$ =400V,  $I_{C}$ =40A  $V_{GE}$ =15V,  $T_{j}$ =175°C  $t_{d(on)}$ Inductive load 10 10 20 0 30 40 50 Gate Resistance :  $R_G[\Omega]$ 

Fig.13 Typical Switching Energy Losses vs. Collector Current 10 Switching Energy Losses [mJ] 1 E<sub>off</sub> Eor 0.1  $V_{CC}$ =400V,  $V_{GE}$ =15V  $R_{G}$ =10 $\Omega$ ,  $T_{j}$ =175°C Inductive load 0.01 50 70 0 20 30 40 60 80 10 Collector Current : I<sub>C</sub> [A]

vs. Gate Resistance 10 Switching Energy Losses [mJ]  $\mathsf{E}_{\mathsf{off}}$ 1 Eon 0.1 V<sub>CC</sub>=400V, I<sub>C</sub>=40A V<sub>GE</sub>=15V, T<sub>j</sub>=175°C Inductive load 0.01 0 10 20 30 40 50 Gate Resistance :  $R_G[\Omega]$ 

Fig.14 Typical Switching Energy Losses

Fig.15 Typical Capacitance vs. Collector To Emitter Voltage 10000 Cies 1000 Capacitance [pF] Coes 100 Cres 10 f=1MHz  $V_{GE}=0V$ T<sub>i</sub>=25°C 0.01 0.1 1 10 100 Collector To Emitter Voltage : V<sub>CE</sub>[V]

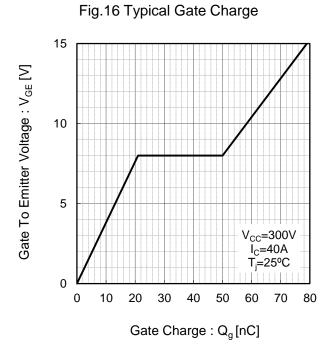
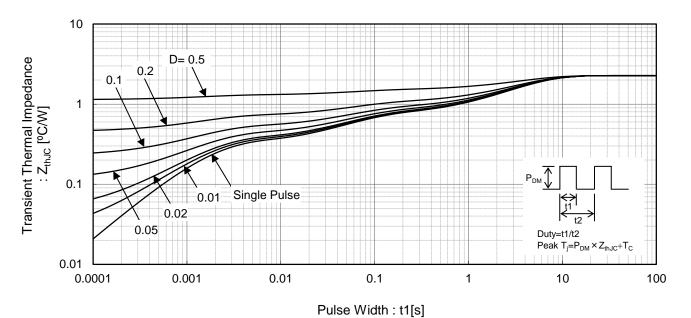


Fig.17 IGBT Transient Thermal Impedance



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### ●Inductive Load Switching Circuit and Waveform

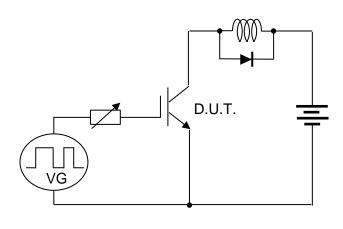


Fig.18 Inductive Load Circuit

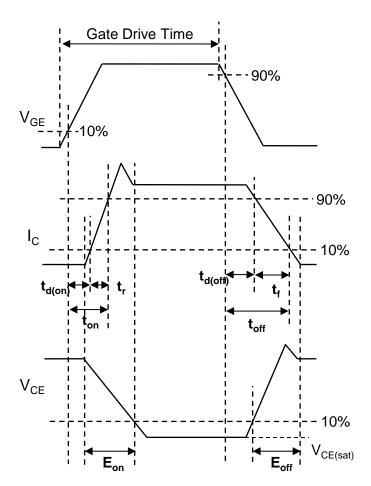


Fig.19 Inductive Load Waveform

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